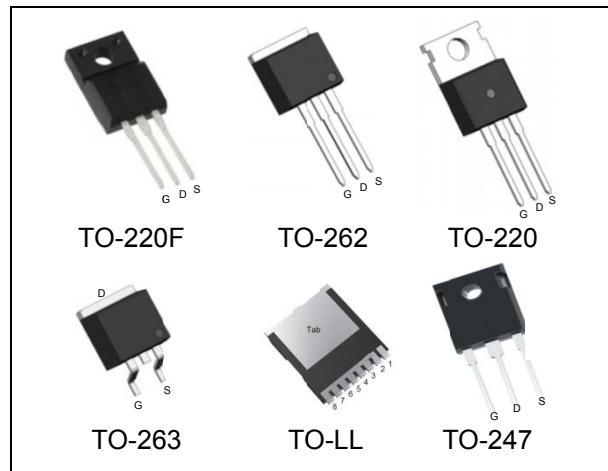


N-channel 250V 9mΩ Power MOSFET

Description

WMOS™ JNM is suitable for applications which require superior power density and outstanding efficiency.

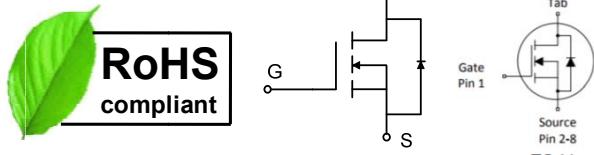


Features

- Gate charge minimized
- Typ. $R_{DS(on)}$ = 9mΩ
- 100% UIS tested
- Pb-free plating, Halogen free

Applications

Switching applications



Absolute Maximum Ratings

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Drain-source voltage	V_{DSS}	250		V
Continuous drain current ¹⁾ ($T_C = 25^\circ\text{C}$)	I_D	120		A
($T_C = 100^\circ\text{C}$)		72		A
Pulsed drain current ²⁾	I_{DM}	360		A
Gate-source voltage	V_{GS}	± 20		V
Avalanche energy, single pulse ³⁾	E_{AS}	650		mJ
Avalanche energy, repetitive ²⁾	E_{AR}	0.3		mJ
Avalanche current, repetitive ²⁾	I_{AR}	4		A
Power dissipation ($T_C = 25^\circ\text{C}$)	P_D	290	34	W
- Derate above 25°C		2.32	0.27	W/°C
Operating and storage temperature range	T_j, T_{stg}	-55 to +150		°C
Continuous diode forward current	I_S	120		A
Diode pulse current	$I_{S,pulse}$	360		A

Thermal Characteristics

Parameter	Symbol	WMK/WMM/WMN/WMJ/WMLL	WML	Unit
Thermal resistance, junction-to-case	$R_{\theta JC}$	0.43	3.6	°C/W
Thermal resistance, junction-to-ambient	$R_{\theta JA}$	62	80	°C/W

Electrical Characteristics $T_c = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{\text{GS}}=0 \text{ V}, I_{\text{D}}=1 \text{ mA}$	250	-	-	V
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=0.25\text{mA}$	2.5	3.5	4.5	V
Drain cut-off current	I_{DSS}	$V_{\text{DS}}=250 \text{ V}, V_{\text{GS}}=0\text{V},$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	-	10	μA
Gate leakage current, forward	I_{GSSF}	$V_{\text{GS}}=20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	500	nA
Drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10 \text{ V}, I_{\text{D}}=20\text{A}$ $T_j = 25^\circ\text{C}$	-	9	11.2	$\text{m}\Omega$
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{\text{DS}}= 100\text{V}, V_{\text{GS}}= 0\text{V},$ $f = 1 \text{ MHz}$	-	5340	-	pF
Output capacitance	C_{oss}		-	163	-	
Reverse transfer capacitance	C_{rss}		-	19	-	
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 100\text{V}, I_{\text{D}} = 30\text{A}$ $R_G = 4.7\Omega, V_{\text{GS}}=10\text{V}$	-	16	-	ns
Rise time	t_r		-	49	-	
Turn-off delay time	$t_{\text{d}(\text{off})}$		-	123	-	
Fall time	t_f		-	8	-	
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{\text{DD}}=160\text{V}, I_{\text{D}}=30\text{A},$ $V_{\text{GS}}=0 \text{ to } 10\text{V}$	-	28	-	nC
Gate to drain charge	Q_{gd}		-	22	-	
Gate charge total	Q_g		-	96	-	
Gate plateau voltage	V_{plateau}		-	5.0	-	V
Reverse diode characteristics						
Diode forward voltage	V_{SD}	$V_{\text{GS}}=0 \text{ V}, I_{\text{F}}=30\text{A}$	-	-	1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{V}, I_{\text{F}}=30\text{A},$ $dI_{\text{F}}/dt=100\text{A}/\mu\text{s}$	-	125	-	ns
Reverse recovery charge	Q_{rr}		-	0.5	-	
Peak reverse recovery current	I_{rrm}		-	8.1	-	A

Notes:

1. Limited by $T_{j\max}$. Maximum duty cycle D=0.5.
2. Repetitive rating: pulse width limited by maximum junction temperature.
3. $I_{AS} = 4\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, starting $T_j = 25^\circ\text{C}$.

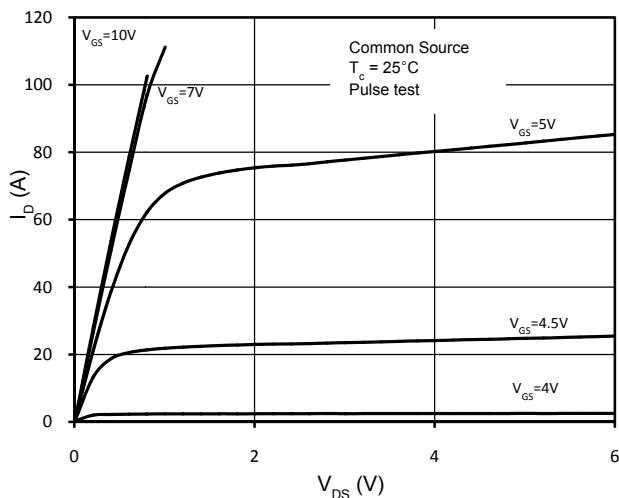


Figure 1. On-Region Characteristics

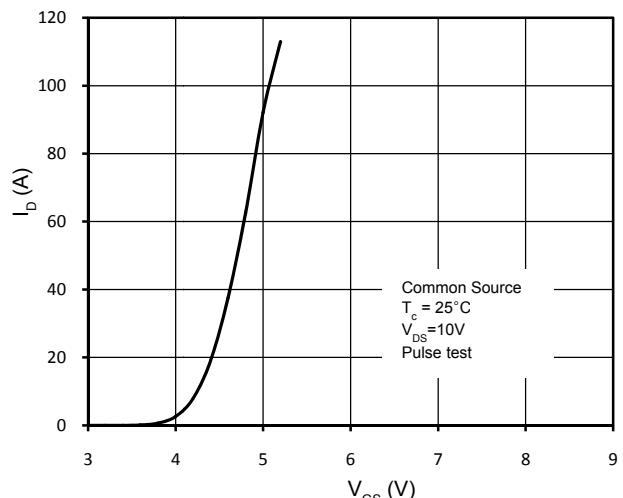


Figure 2. Transfer Characteristics

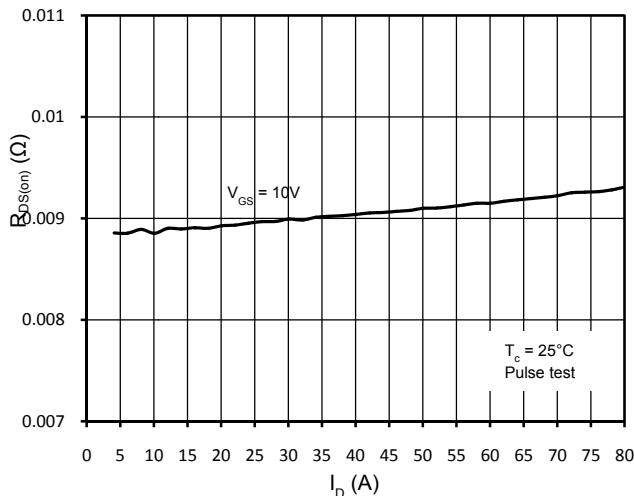


Figure 3. Static Drain-Source On Resistance

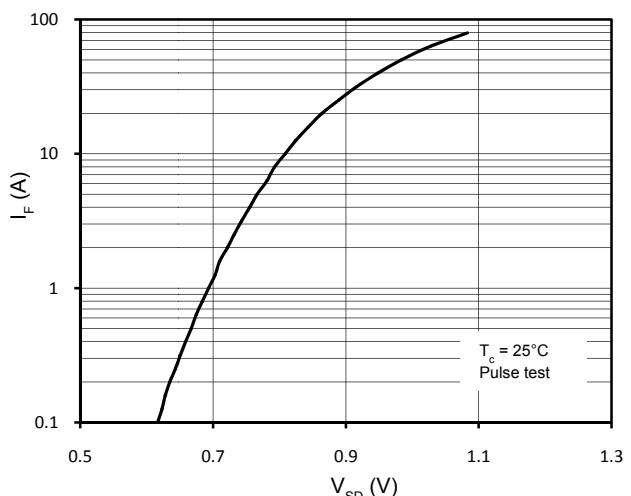
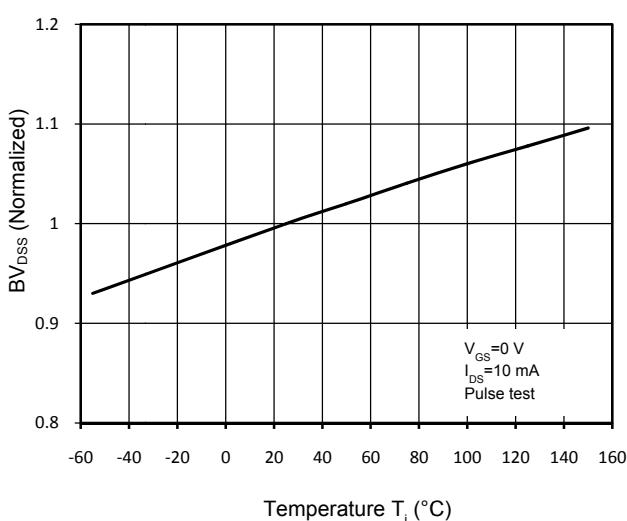
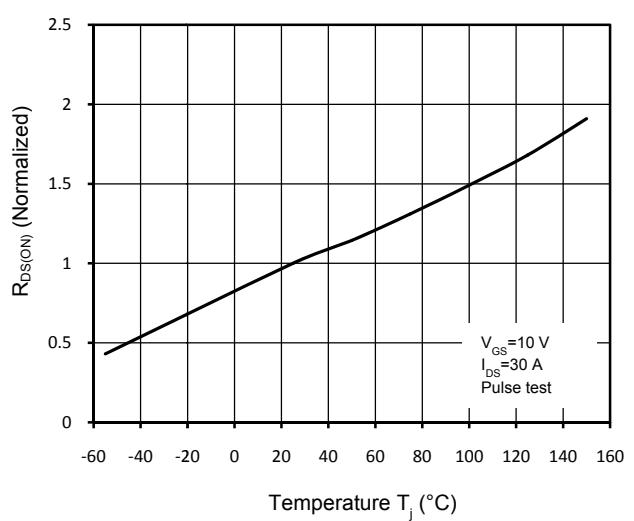


Figure 4. Body-Diode Forward Characteristics

Figure 5. Normalized BV_{DSs} vs. TemperatureFigure 6. Normalized $R_{DS(on)}$ vs. Temperature

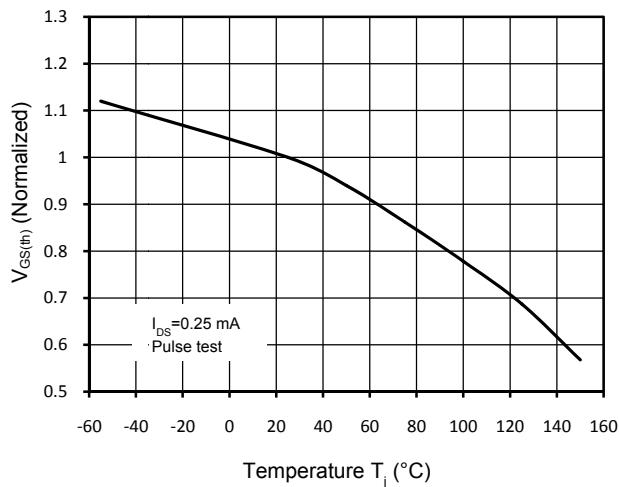


Figure 7. Threshold Voltage vs. Temperature

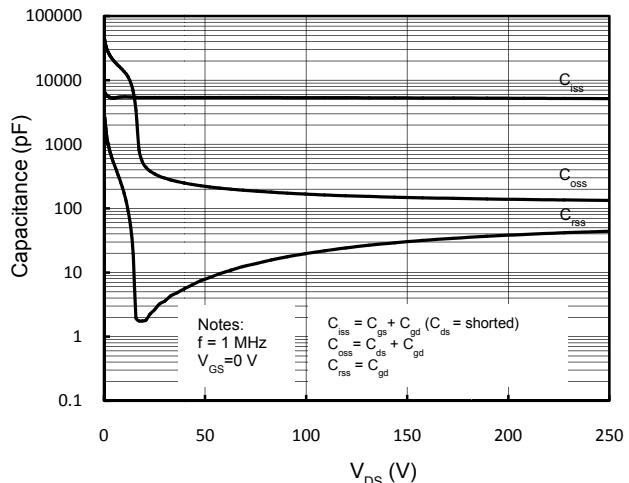


Figure 8. Capacitance Characteristics

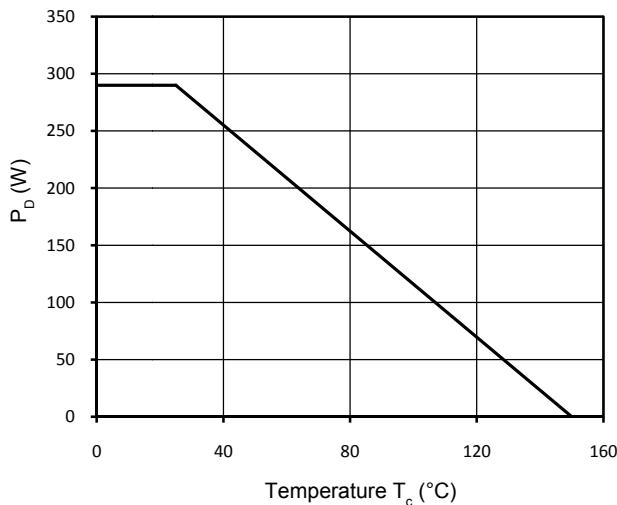


Figure 9. Power Dissipation

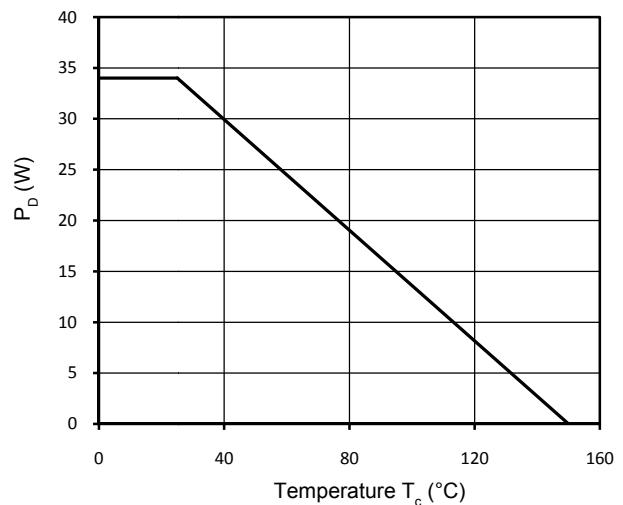


Figure 10. Power Dissipation (TO-220F)

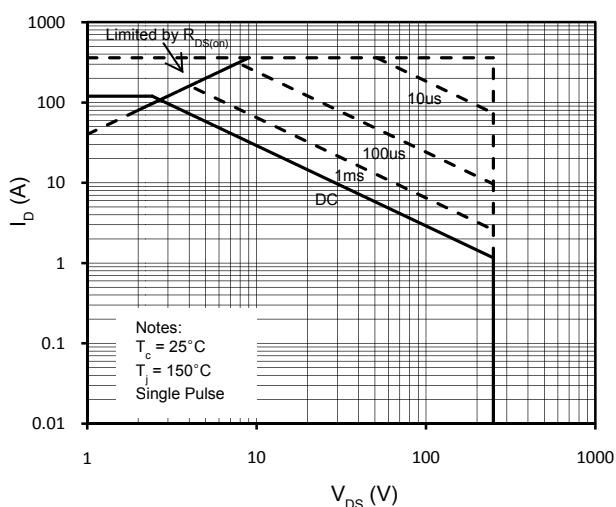


Figure 11. Maximum Safe Operating Area

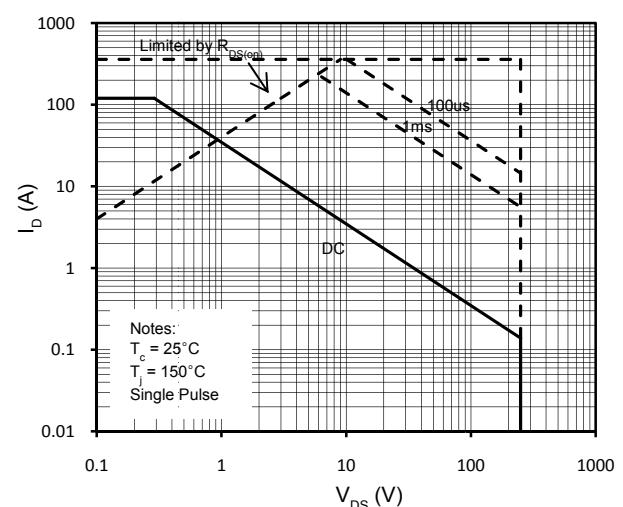


Figure 12. Maximum Safe Operating Area(TO-220F)

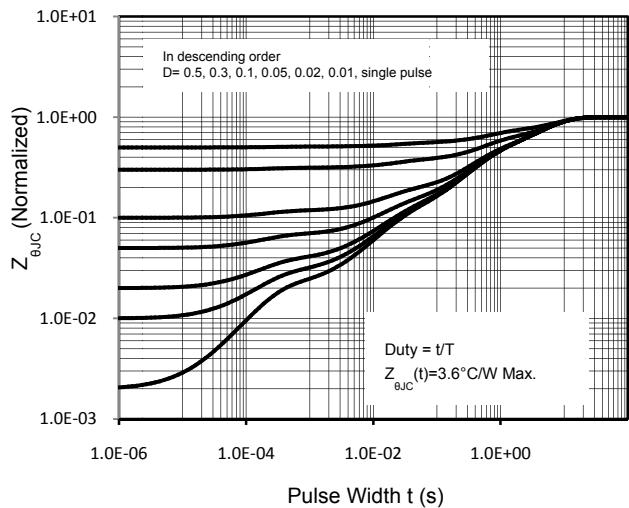


Figure 13. Transient Thermal Response Curve (TO-220F)

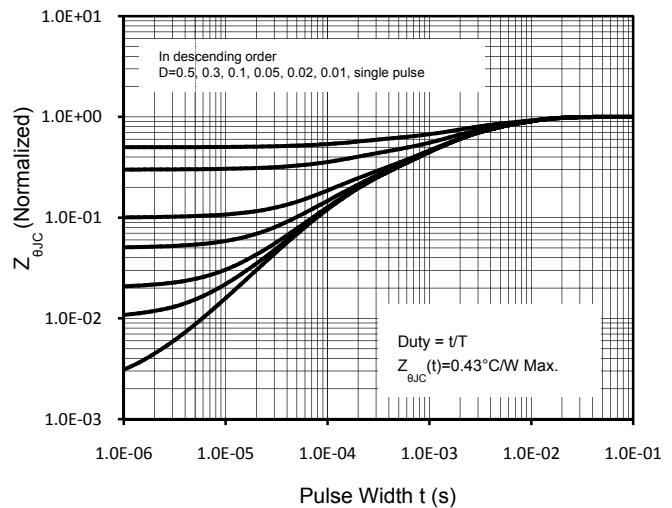


Figure 14. Transient Thermal Response Curve

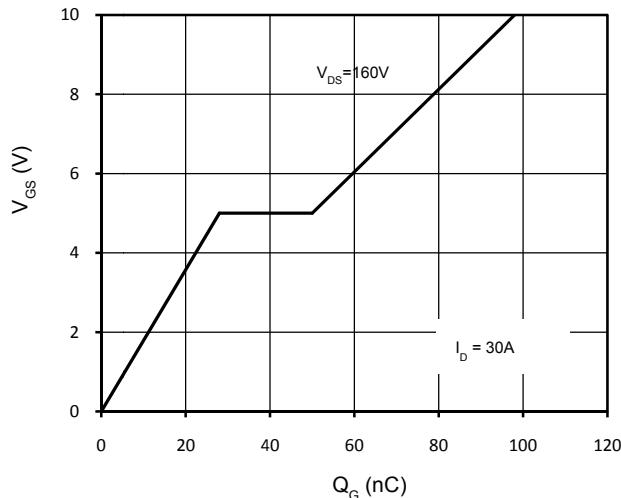
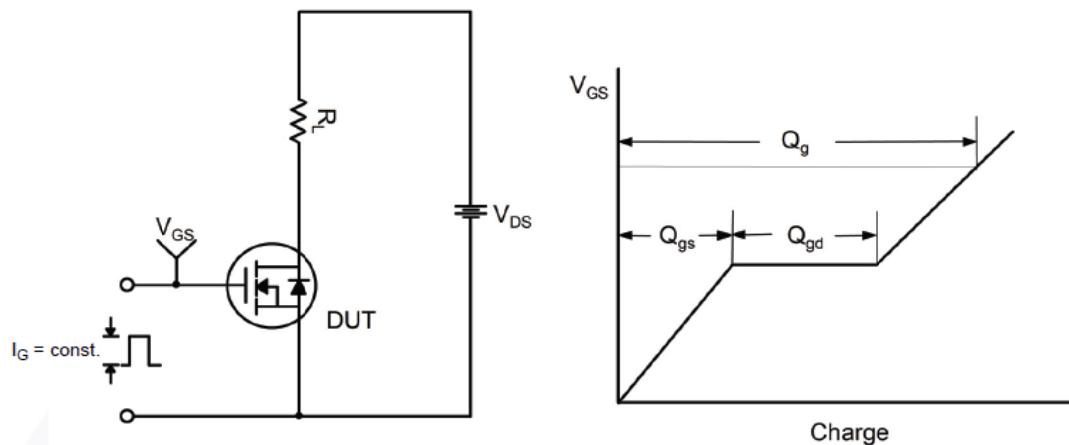
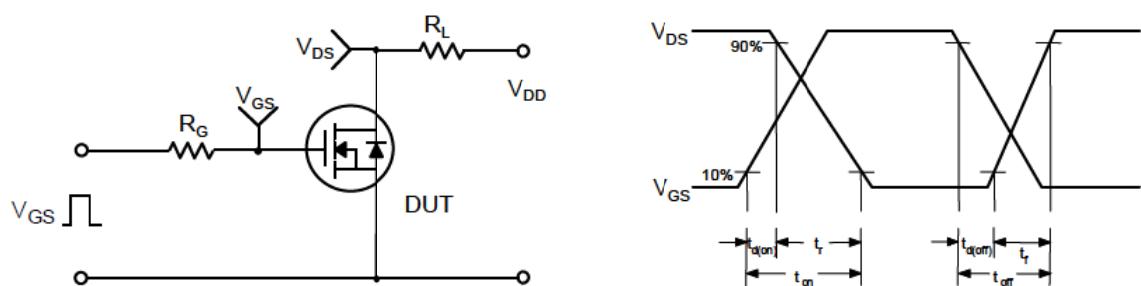
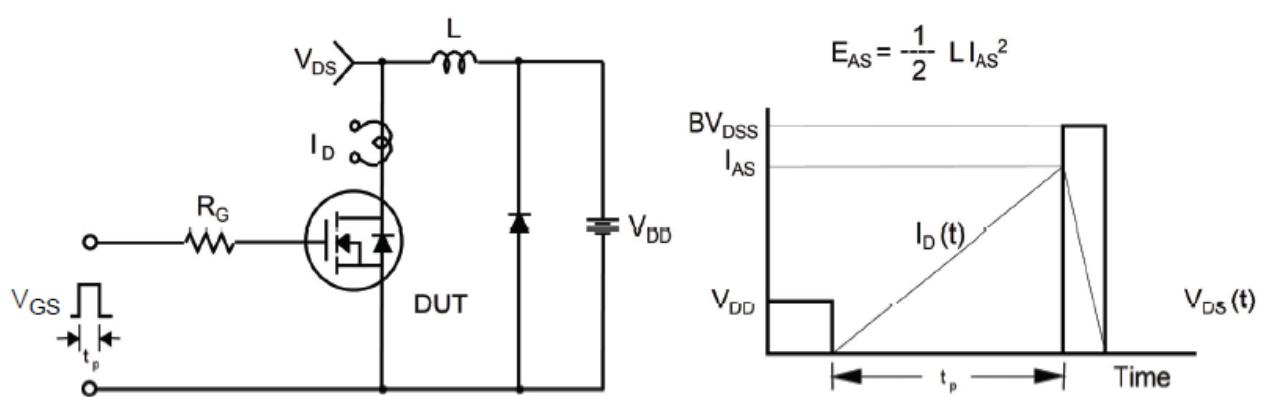
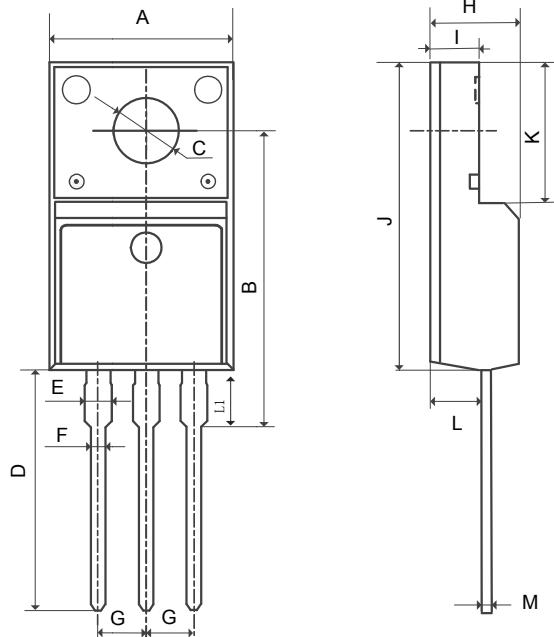
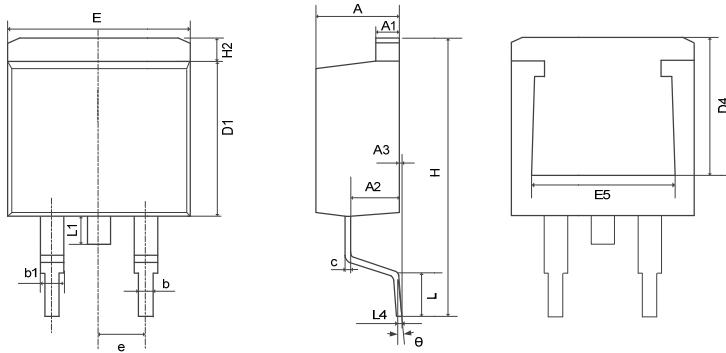


Figure 15. Gate Charge Characteristics

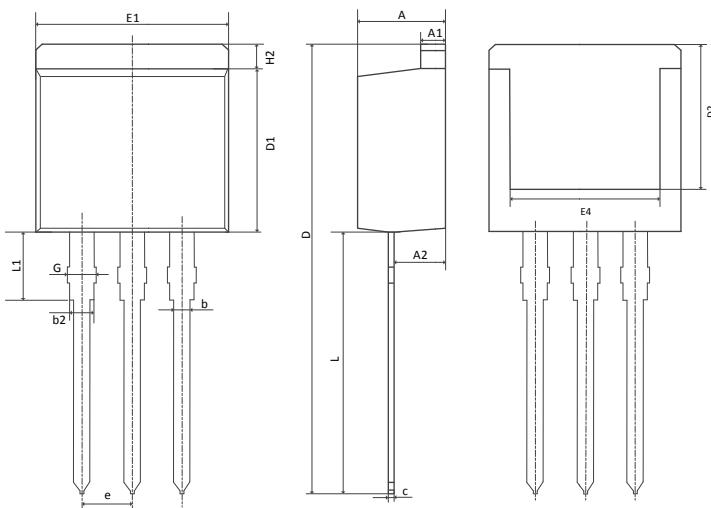
Gate Charge Test Circuit & Waveform**Switching Test Circuit & Waveforms****Unclamped Inductive Switching Test Circuit & Waveforms**

Mechanical Dimensions for TO-220F**COMMON DIMENSIONS**

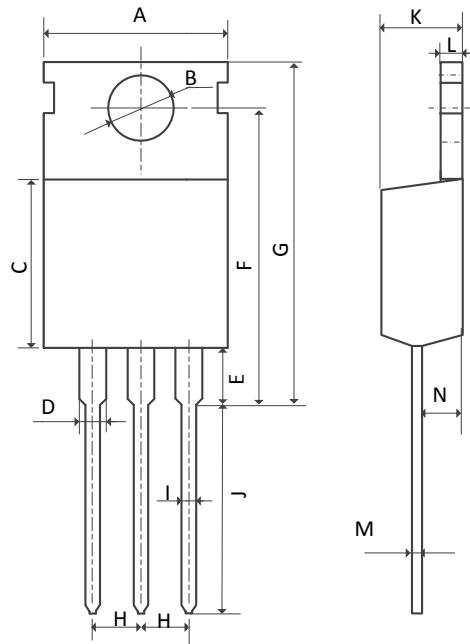
SYMBOL	MM	
	MIN	MAX
A	9.96	10.36
B	15.10	16.10
C	3.03	3.38
D	12.64	13.28
E	1.18	1.58
F	0.70	0.95
G	2.54REF	
H	4.50	4.90
I	2.34	2.74
J	15.57	16.17
K	6.70REF	
L	2.56	2.96
M	0.40	0.65
L1	2.85	3.45

Mechanical Dimensions for TO-263**COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	4.37	4.89
A1	1.17	1.42
A2	2.19	2.89
b	0.70	0.96
b1	1.17	1.47
c	0.30	0.60
D1	8.45	9.35
D4	6.60	—
E	9.80	10.40
E5	7.06	—
e	2.54BSC	
H	14.70	16.00
H2	1.07	1.47
L	2.00	2.70
L1	1.15	1.75
L4	0.25BSC	
θ	0°	9°

Mechanical Dimensions for TO-262
COMMON DIMENSIONS


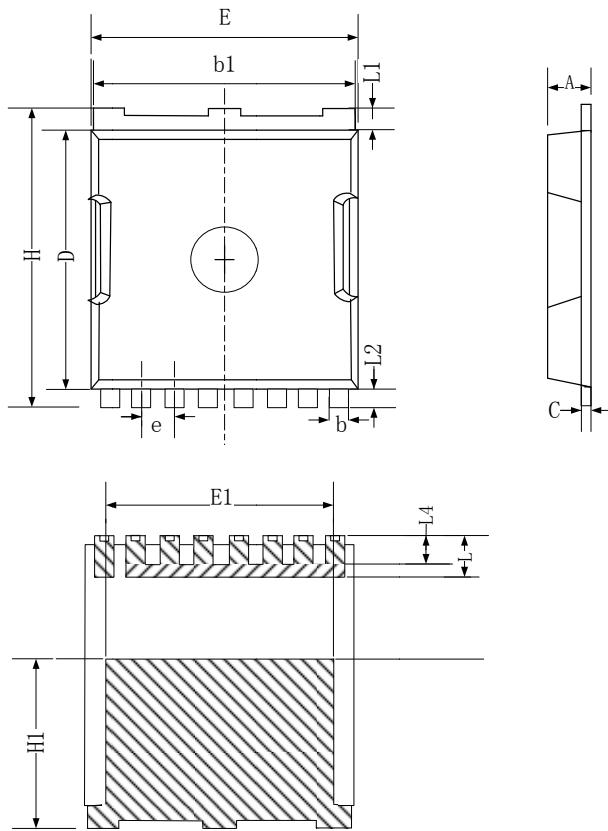
SYMBOL	MM	
	MIN	MAX
A	4.37	4.90
A1	1.17	1.42
A2	2.2	2.89
b	0.71	0.96
b2	1.07	1.47
c	0.28	0.6
D	22.00	24.02
D1	8.45	9.3
D2	6.00	—
E1	9.8	10.40
E4	7.06	—
e	2.54BSC	
G	1.23	1.50
H2	—	1.50
L	12.90	14.16
L1	2.80	4.00

Mechanical Dimensions for TO-220**COMMON DIMENSIONS**

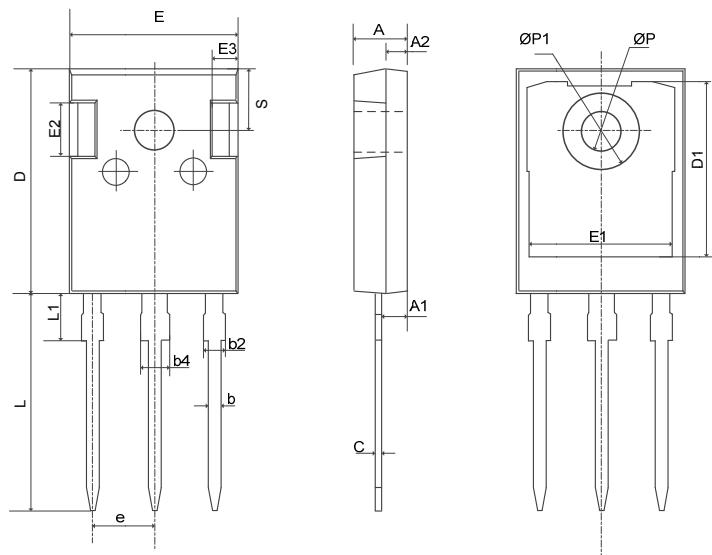
SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.90
G	19.60MAX	
H	2.54REF	
I	0.70	0.95
J	9.25	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Mechanical Dimensions for TO-LL

COMMON DIMENSIONS



SYMBOL	MM	
	MIN	MAX
A	2.15	2.45
b	0.7	0.95
b1	9.6	9.95
C	0.4	0.6
D	10.1	10.6
E	9.6	10.1
E1	7.9	8.5
e	1.20BSC	
H	11.38	11.88
H1	6.65	7.2
L	1.4	2
L1	0.5	0.9
L2	0.48	0.72
L4	1	1.3

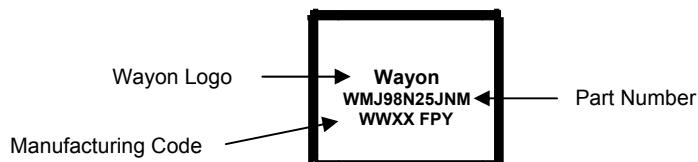
Mechanical Dimensions for TO-247**COMMON DIMENSIONS**

SYMBOL	MM	
	MIN	MAX
A	4.80	5.21
A1	2.21	2.61
A2	1.85	2.16
b	1.07	1.36
b2	1.91	2.41
b4	2.87	3.38
c	0.51	0.75
D	20.70	21.30
D1	16.25	17.65
E	15.50	16.13
E1	12.38	13.60
E2	3.68	5.20
E3	1.00	2.70
e	5.44BSC	
L	19.62	20.32
L1	—	4.40
ØP	3.40	3.80
ØP1	—	7.30
S	6.15BSC	

Ordering Information

Part	Package	Marking	Packing method
WML98N25JNM	TO-220F	WML98N25JNM	Tube
WMK98N25JNM	TO-220	WMK98N25JNM	Tube
WMN98N25JNM	TO-262	WMN98N25JNM	Tube
WMM98N25JNM	TO-263	WMM98N25JNM	Tape and Reel
WMLL98N25JNM	TO-LL	WMLL98N25JNM	Tape and Reel
WMJ98N25JNM	TO-247	WMJ98N25JNM	Tube

Marking Information



Contact Information

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Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: <http://www.way-on.com>

For additional information, please contact your local Sales Representative.

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